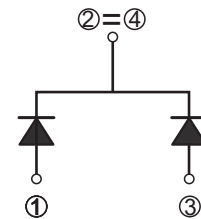
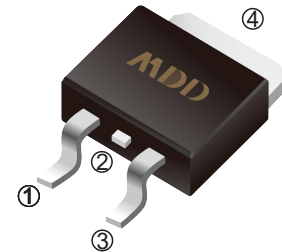


## FAST RECOVERY EPI DIODES

### Features

- ◆ High frequency operation
- ◆ High surge forward current capability
- ◆ High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- ◆ Guard ring for enhanced ruggedness and long term reliability

TO-252(D-PAK)



### Mechanical Data

**Case:** TO-252 molded plastic body

**Terminals:** Plated axial leads, solderable per MIL-STD-750, Method 2026

**Polarity:** Color band denotes cathode end

**Mounting Position:** Any

**Weight:** 0.0141 ounce (approx), 0.4 grams (approx)

### Maximum Ratings And Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

CHARACTERISTICS	SYMBOL	MDD MURD1620D	MDD MURD1640D	MDD MURD1660D	UNITS
Maximum repetitive peak reverse voltage	$V_{RRM}$	200	400	600	V
Maximum RMS voltage	$V_{RMS}$	140	280	420	V
Maximum DC blocking voltage	$V_{DC}$	200	400	600	V
Maximum average forward rectified current	$I_{(AV)}$	16			A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	$I_{FSM}$	100			A
Maximum instantaneous forward voltage at 8.0A	$V_F$	1.0	1.30	1.6	V
Maximum DC reverse current at rated DC blocking voltage $T_A=25^\circ\text{C}$ $T_A=125^\circ\text{C}$	$I_R$	10 100			$\mu\text{A}$
Typical junction capacitance (NOTE 1)	$C_J$	45			pF
Typical thermal resistance (NOTE 2)	$R_{\theta JA}$	50			$^\circ\text{C}/\text{W}$
Maximum Reverse Recovery Time (Note 3)	$T_{rr}$	35			ns
Operating junction and storage temperature range	$T_J, T_{STG}$	-55 to +175			$^\circ\text{C}$

**Note:** 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

2. Thermal resistance from junction to case.

3. Reverse Recovery Test Conditions:  $I_F=0.5\text{A}$ ,  $I_R=1\text{A}$ ,  $I_{rr}=0.25\text{A}$ .

## Rating and Characteristic Curves

Fig.1 Maximum Average Forward Current Rating

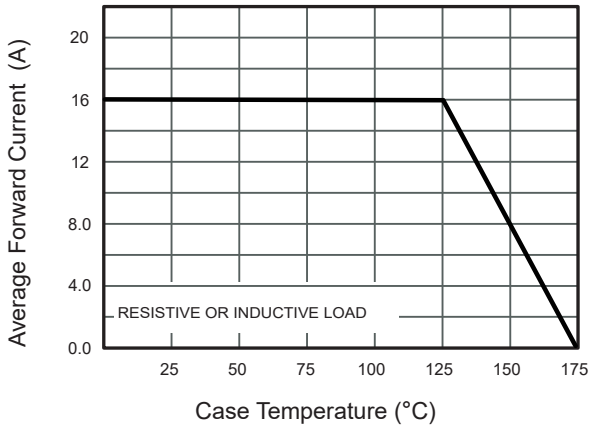


Fig.2 Typical Reverse Characteristics

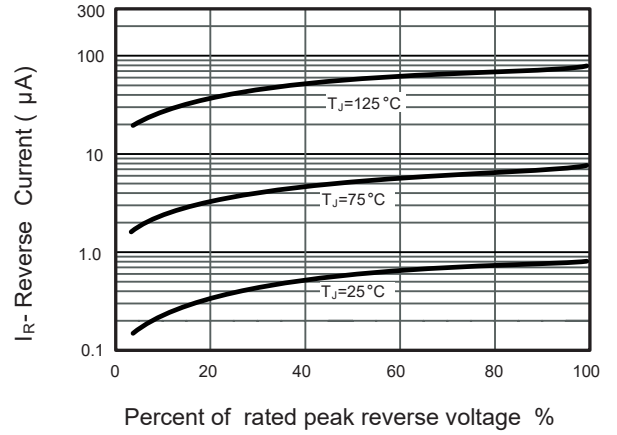


Fig.4 Typical Forward Characteristics

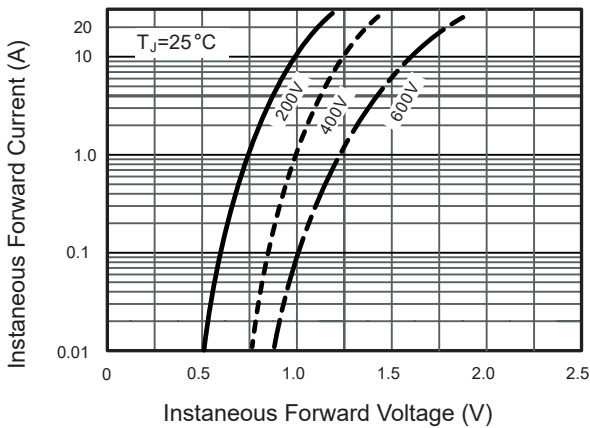


Fig.4 Typical Junction Capacitance

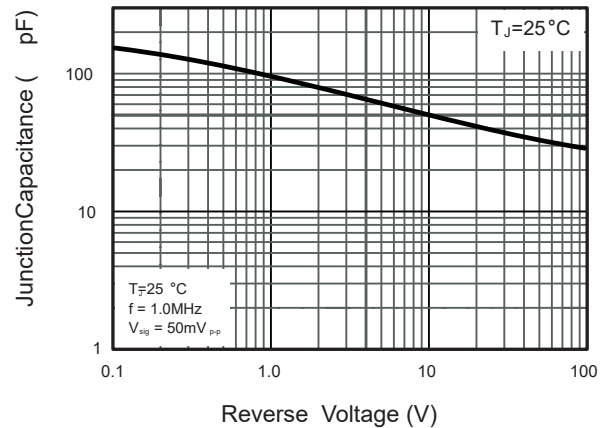


Fig.5 Maximum Non-Repetitive Peak Forward Surge Current

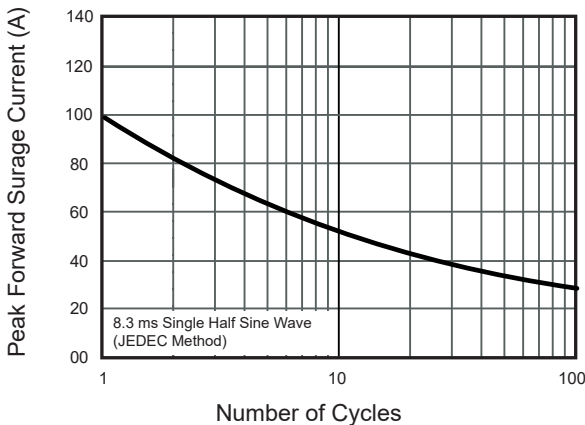
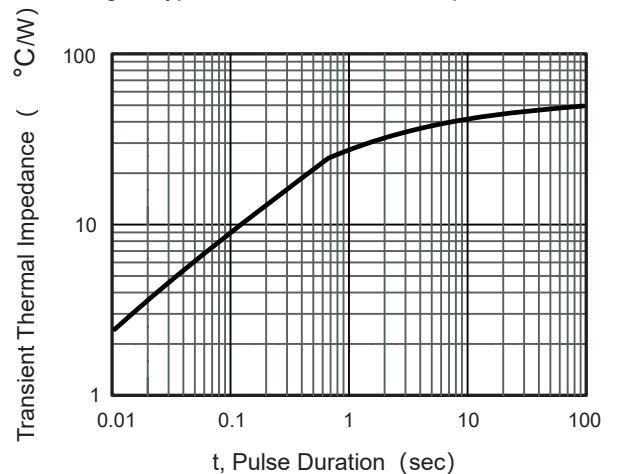


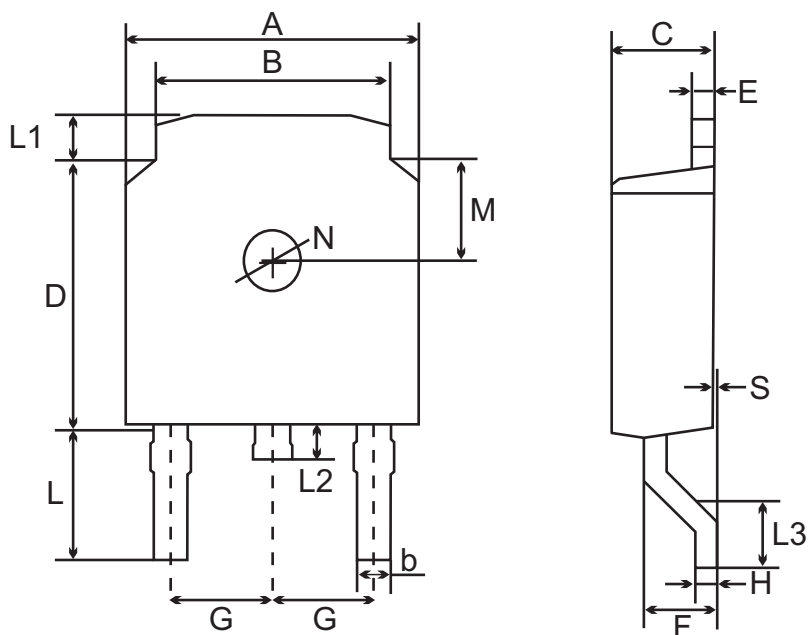
Fig.6- Typical Transient Thermal Impedance



The curve above is for reference only.

## Outline Drawing

TO-252(D-PAK) Package Outline Dimensions



TO-252(D-PAK) mechanical data

UNIT		A	B	b	C	D	E	F	G	H	L	L1	L2	L3	S	M	N
mm	max	6.7	5.53	0.86	2.5	6.3	0.6	1.8	2.29 TYPICAL	0.60	3.4	1.2	1.0	1.75	0.15	1.98	1.3
	min	6.3	5.1	0.66	2.1	5.9	0.4	1.3		0.40	2.7	0.8	0.6	1.40	0.0	1.58	1.2

## Important Notice and Disclaimer

Microdiode Electronics (Shenzhen) reserves the right to make changes to this document and its products and specifications at any time without notice. Customers should obtain and confirm the latest product information and specifications before final design, purchase or use.

Microdiode Electronics (Shenzhen) makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Microdiode Electronics (Shenzhen) assume any liability for application assistance or customer product design. Microdiode Electronics (Shenzhen) does not warrant or accept any liability with products which are purchased or used for any unintended or unauthorized application.

No license is granted by implication or otherwise under any intellectual property rights of Microdiode Electronics (Shenzhen).

Microdiode Electronics (Shenzhen) products are not authorized for use as critical components in life support devices or systems without express written approval of Microdiode Electronics (Shenzhen).